(b) Amendment to the Claims

Please cancel claims 5, 7, 9, 19, 21 and 23 without prejudice or disclaimer.

Kindly amend claims 1, 6, 10-15, 20 and 24-28 as follows. A detailed listing of all the claims is provided.

1. (Currently Amended) An exhaust processing method of exhausting a processing space for subjecting a substrate or a film to plasma processing, which comprises:

(a) providing chemical-reaction inducing means comprising a heating element comprising a first metal member connected to a power source in an exhaust line connecting the processing space to exhaust means; [[and]]

(b) providing a plasma blocking means comprising a second metal member electrically grounded between the processing space and the first metal member; and

(c) causing chemical reaction of at least either an unreacted gas [[of]] or a by-product exhausted from the processing space via heat from said heating element while blocking plasma in the processing space from reaching the chemical-reaction inducing means via said plasma blocking means ~~to chemically react without allowing plasma in the processing space to reach the chemical-reaction inducing means;~~

~~wherein the chemical reaction of at least either the unreacted gas or the byproduct exhausted from the processing space is caused by heating of the chemical-reaction inducing means;~~

~~wherein a metal member is the chemical-reaction inducing means; and~~

~~wherein the metal member is at least one of chromium, molybdenum, [illegible] tungsten, vanadium, niobium, tantalum, titanium, zirconium or hafnium.~~

2. - 5. (Cancelled)

6. (Currently Amended) The exhaust processing method according to claim [[5,]] 1, wherein a conductive member is provided as the means for blocking plasma and has a potential different from that in a plasma space.

7. (Cancelled)

8. (Previously Presented) The exhaust processing method according to claim 6, wherein a material used for the chemical-reaction inducing means is the same as used for the conductive member.

9. (Cancelled)

10. (Currently Amended) The exhaust processing method according to claim [[5,]] 1, wherein one or more linear members or a linear member formed by a spiral winding are used as the means for blocking plasma.

11. (Currently Amended) The exhaust processing method according to claim [[5,]] 1, wherein a mesh is used as the means for blocking plasma.

12. (Currently Amended) The exhaust processing method according to claim [[5,]] 1, wherein a plate-shaped member having a shape for preventing passage of the plasma is used as the means for blocking plasma.

13. (Currently Amended) The exhaust processing method according to claim [[5,]] 1, wherein a plate-shaped member with openings is used as the means for blocking plasma.

14. (Currently Amended) The exhaust processing method according to claim [[5,]] 1, wherein a plate-shaped member is used as the means for blocking plasma, and the plate-shaped member is arranged in the exhaust line so that a gap is provided between the plate-shaped member and an inner wall of the exhaust line.

15. (Currently Amended) A plasma processing method for subjecting a substrate or a film to plasma processing, which comprises:

(a) arranging a chemical-reaction inducing means comprising a heating element comprising a first metal member connected to a power source in an exhaust line connecting a processing space for plasma processing to exhaust means for exhausting the processing space; [[and]]

(b) providing a plasma blocking means comprising a second metal member electrically grounded between the processing space and the first metal member; and

(c) causing chemical reaction of at least either an unreacted gas or a by-product exhausted from the processing space via heat from said heating element while blocking plasma in the processing space from reaching the chemical reaction inducing means via said plasma blocking means ~~without allowing plasma in the processing space to reach the chemical-reaction inducing means;~~

~~wherein the chemical reaction of at least either the unreacted gas or byproduct exhausted from the processing space is caused by heating of the chemical-reaction inducing means;~~

~~wherein a metal member is the chemical-reaction inducing means, and~~

~~wherein the metal member is at least one of chromium, molybdenum, tungsten, vanadium, niobium, tantalum, titanium, zirconium or hafnium.~~

16. - 19. (Cancelled)

20. (Currently Amended) The plasma processing method according to claim [[19,]] 15, wherein a conductive member is provided as the means for blocking plasma and has a potential different from that in a plasma space.

21. (Cancelled)

22. (Previously Presented) The plasma processing method according to claim 20, wherein a material used for the chemical-reaction inducing means is the same as used for the conductive member.

23. (Cancelled)

24. (Currently Amended) The plasma processing method according to claim [[19,]] 15, wherein one or more linear members or a linear member formed by a spiral winding are used as the means for blocking plasma.

25. (Currently Amended) The plasma processing method according to claim [[19,]] 15, wherein a mesh is used as the means for blocking plasma.

26. (Currently Amended) The plasma processing method according to claim [[19,]] 15, wherein a plate-shaped member having a shape for preventing passage of the plasma is used as the means for blocking plasma.

27. (Currently Amended) The plasma processing method according to claim [[19,]] 15, wherein a plate-shaped member with openings is used as the means for blocking plasma.

28. (Currently Amended) The plasma processing method according to claim [[19,]] 15, wherein a plate-shaped member is used as the means for blocking plasma, and the plate-shaped member is arranged in the exhaust line so that a gap is provided between the plate-shaped member and an inner wall of the exhaust line.

29. (Original) The plasma processing method according to claim 15, wherein the plasma processing is film formation conducted by a plasma CVD process.

30. (Original) The plasma processing method according to claim 15, wherein the plasma processing is plasma etching a substrate or a film.

31-50. (Cancelled)